

MANIFESTATION
OF THE LASER-SHOCK-WAVE-INDUCED
DIFFUSION OF DOPANTS BELONGING
TO THE FIRST GROUP OF ELEMENTS
IN $\text{Hg}_{0.8}\text{Cd}_{0.2}\text{Te}$

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S u m m a r y

The influence of laser-induced shock waves (LISWs) on narrow-gap semiconductors with high nonequilibrium concentrations of dopants has been considered, with the structures $\text{Hg}_{0.8}\text{Cd}_{0.2}\text{Te}/\text{Me}$ ($\text{Me} = \text{Cu}, \text{Au}$) being taken as an example. The possibility of the dopant diffusion stimulated by LISWs from a layer on the semiconductor surface, which is nonuniform by concentration, into the bulk of the specimen has been demonstrated. It has been confirmed that the rapid diffusion of dopants belonging to elements of the first group and possessing high concentrations is accompanied by the creation of new compounds.